

### **INCHANGE SEMICONDUCTOR**

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## **isc** Silicon PNP Power Transistor

# 2SB1019

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<ul> <li>DESCRIPTION</li> <li>Low Collector Saturation Voltage- : V<sub>CE(sat)</sub>= -0.4V(Max)@I<sub>C</sub>= -4A</li> <li>Good Linearity of h<sub>FE</sub></li> <li>Complement to Type 2SD1412</li> <li>Minimum Lot-to-Lot variations for robust device performance and reliable operation</li> </ul>				12	3		3 1 Bas 2 Col 3 Emi 20Fa p	lect
Power	TIONS urrent switching applications. amplifier applications. TE MAXIMUM RATINGS(Ta=2.	© 5°C)			B G G	→ S •	• .	Ć
SYMBOL	PARAMETER	VALUE	UNIT		th th			n h
V <sub>CBO</sub>	Collector-Base Voltage	-70	v	Ķ	ųμ			
V <sub>CEO</sub>	Collector-Emitter Voltage	-50	V		ļļ			
$V_{\text{EBO}}$	Emitter-Base Voltage	-5	V			→ R ≪C	-	-N
lc	Collector Current-Continuous	-7	Α		DIM	MIN	m Max	3
		-			A	16.85	17.15	
IB	Base Current-Continuous	-1	A		B C	9.54	10.10	-
IB	Dase ourient-continuous		~		D	0.75	4.65 0.90	
Pc	Collector Power Dissipation @ $T_a=25^{\circ}C$ Collector Power Dissipation @ $T_c=25^{\circ}C$	2 30			F	3.20	3.40	
			W		G	6.90	7.20	
					H J	5.15 0.45	5.45	
					K	13.35	0.75	1
					L	1.10	1.30	
					N	4.98	5.18	
	Junction Temperature	150	°C		Q	4.85	5.15	
TJ	Junction remperature							- 1 C
TJ					R	2.55	3.25	8
TJ T <sub>stg</sub>	Storage Temperature Range	-55~150	°C		R S U	2.55 2.70 1.75	3.25 2.90 2.05	2



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### **ELECTRICAL CHARACTERISTICS**

#### T<sub>c</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	мах	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	Ic= -30mA; I <sub>B</sub> = 0	-50			V
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -4A; I <sub>B</sub> = -0.4A			-0.4	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -4A; I <sub>B</sub> = -0.4A			-1.2	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = -70V; I <sub>E</sub> = 0			-30	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-50	μA
h <sub>FE-1</sub>	DC Current Gain	Ic= -1A; Vc= -1V	70		240	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -4A; V <sub>CE</sub> = -1V	30			

#### h<sub>FE-1</sub> Classifications

0	Y		
70-140	120-240		

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